



Bipolar PNP Bare Die – BTP190

Part Description

The BTP190 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = -40V
- VCEO = -40V
- VEBO = -5V
- hFE = 90-333 @ VCE = -1V, IC = -0.01A
- VCE(Sat) = -0.4V @ IC = -0.05A, IB = -5mA
- fT = 250 MHz @ VCE = -20V, IE = 0A
- COBO = 4pF @ VCB = -5V

Features

Low VCE(sat)

Die Size (Unawn)

300µm X 520µm, 12 Mils X 20 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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